

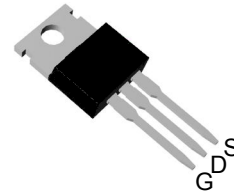
Features

- 60V/55A,
 $R_{DS(ON)} = 11m\Omega$ (typ.) @ $V_{GS} = 10V$
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

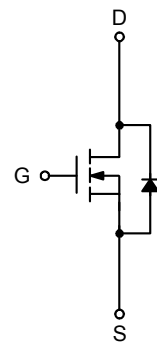
Applications

- Synchronous Rectification.
- Power Management in Inverter Systems.

Pin Description



Top View of TO-220



N-Channel MOSFET

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}\text{C}$	A
I_{DP}	300 μs Pulse Drain Current Tested	$T_C=25^{\circ}\text{C}$	A
I_D	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	A
		$T_C=100^{\circ}\text{C}$	
P_D	Maximum Power Dissipation	$T_C=25^{\circ}\text{C}$	W
		$T_C=100^{\circ}\text{C}$	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.8	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	
E_{AS}	Avalanche Energy, Single Pulsed	L=1mH	mJ

Electrical Characteristics ($T_A = 25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions				Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =30A	-	11	14	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =30A, V _{GS} =0V	-	0.85	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =30A,	-	45	-	ns
Q _{rr}	Reverse Recovery Charge	di _{SD} /dt=100A/μs	-	60	-	nC

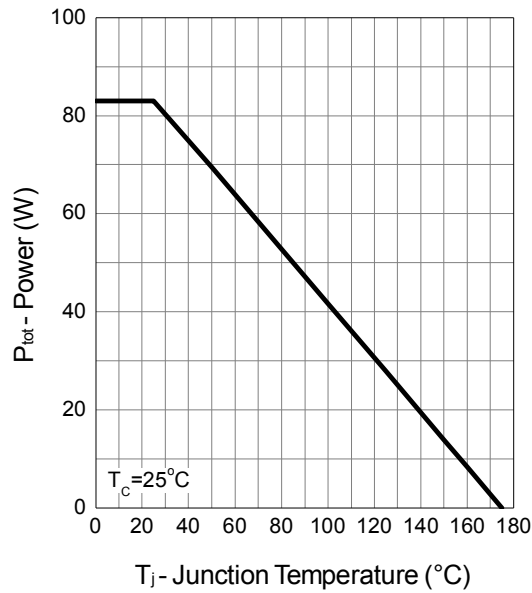
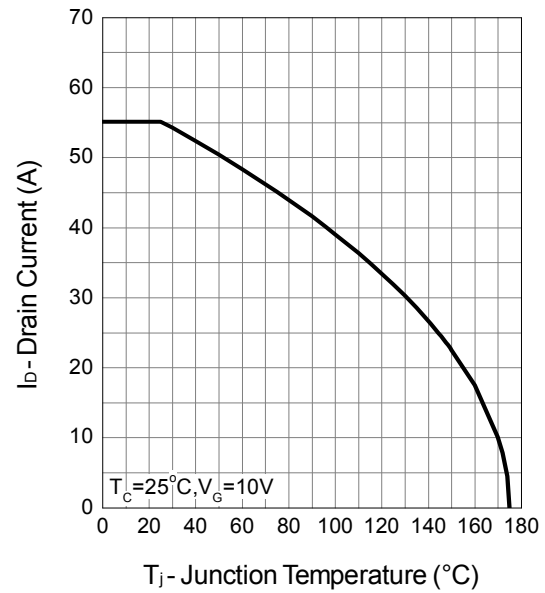
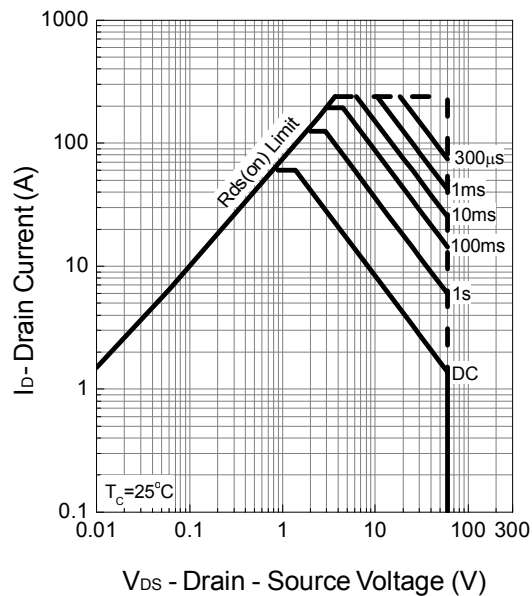
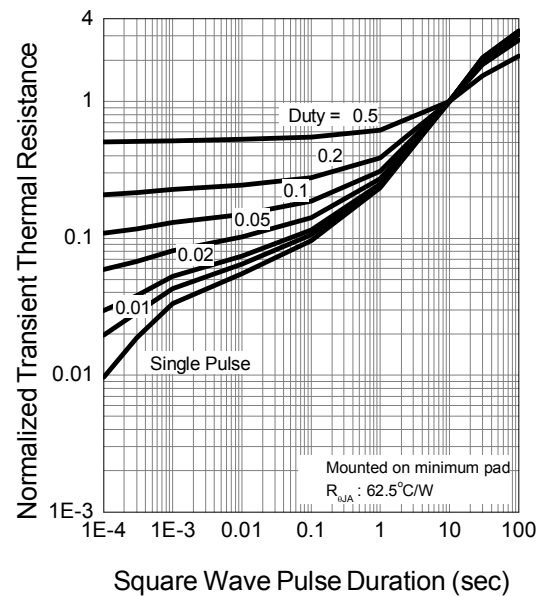
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions				Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	2400	-	pF
C _{oss}	Output Capacitance		-	245	-	
C _{rss}	Reverse Transfer Capacitance		-	140	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	20	30	ns
t _r	Turn-on Rise Time		-	18	33	
t _{d(OFF)}	Turn-off Delay Time		-	50	90	
t _f	Turn-off Fall Time		-	25	45	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =30A	-	45	63	nC
Q _{gs}	Gate-Source Charge		-	15	-	
Q _{gd}	Gate-Drain Charge		-	15	-	

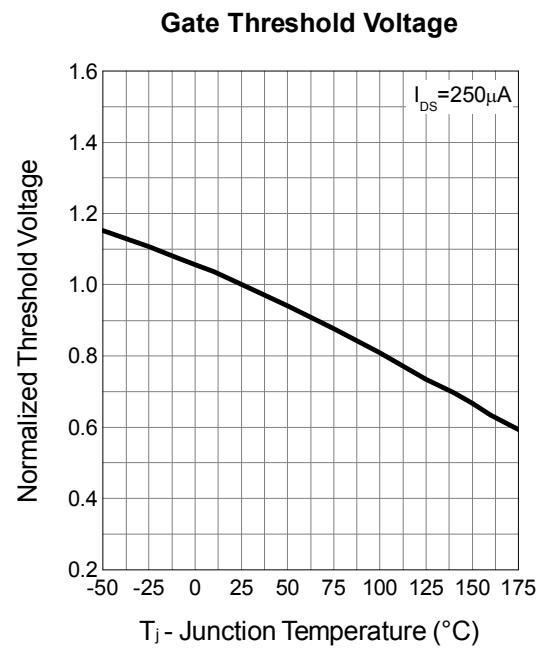
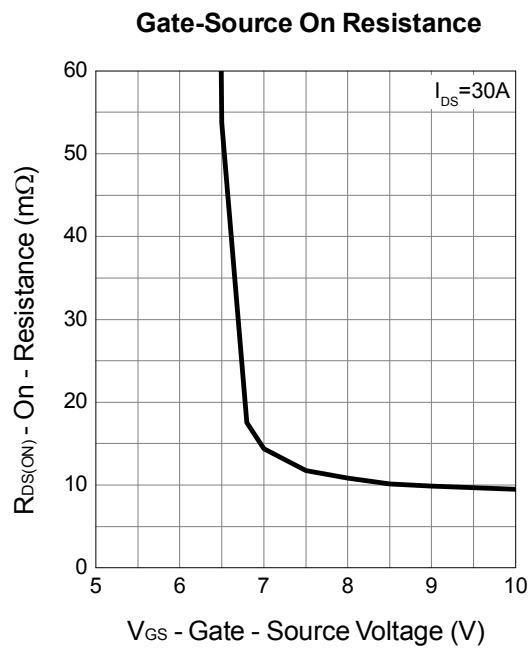
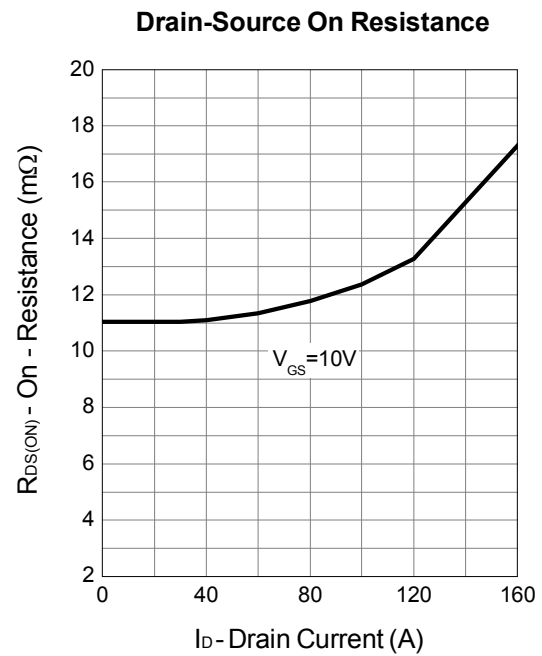
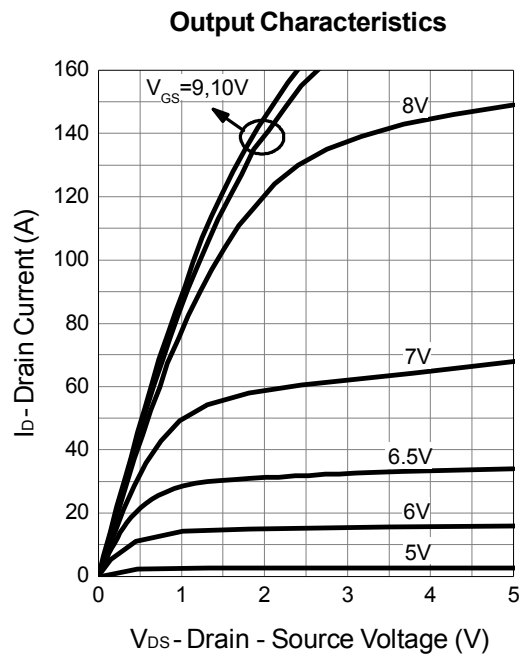
Note a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

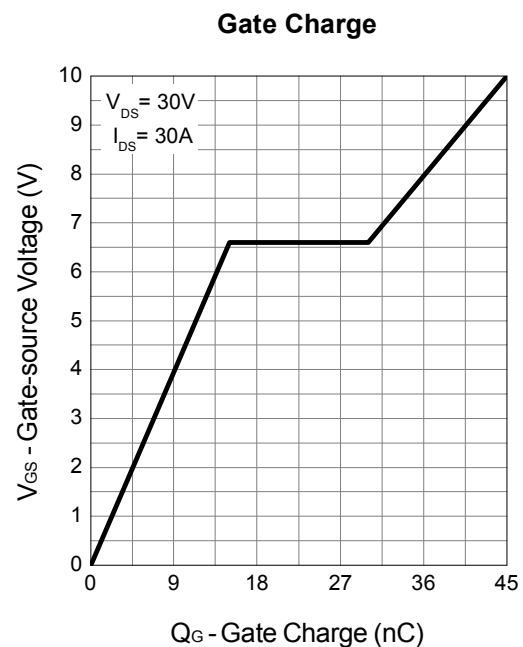
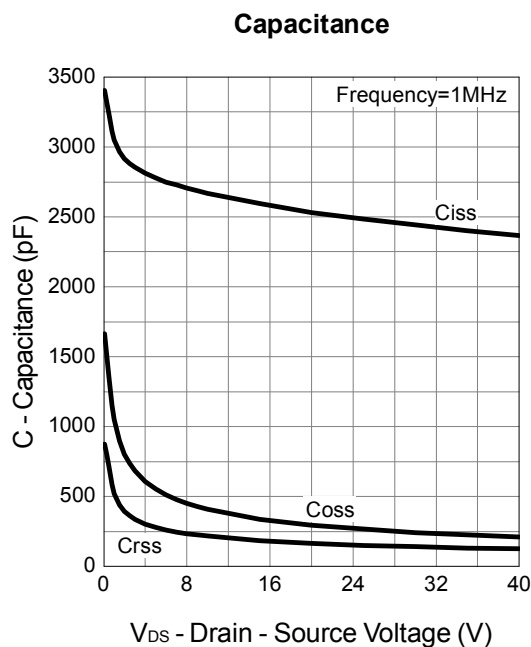
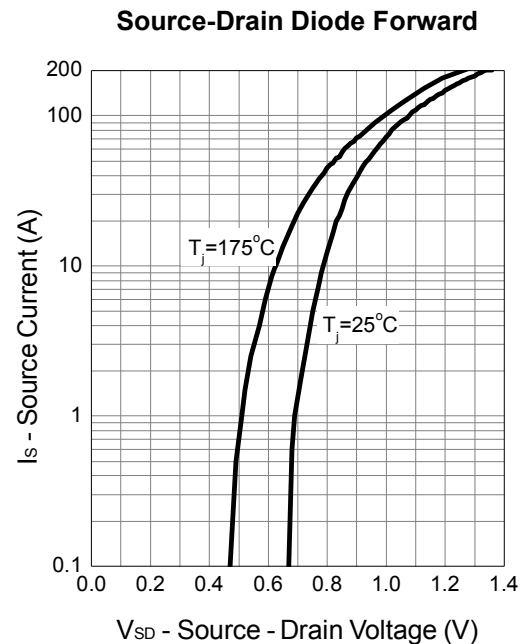
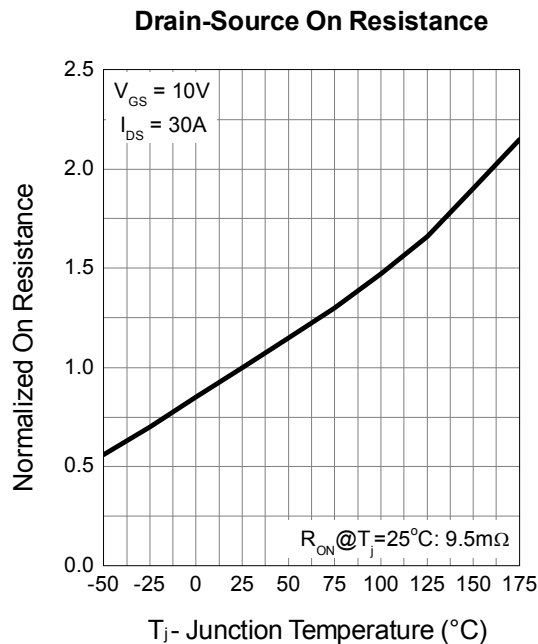
Typical Operating Characteristics

Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


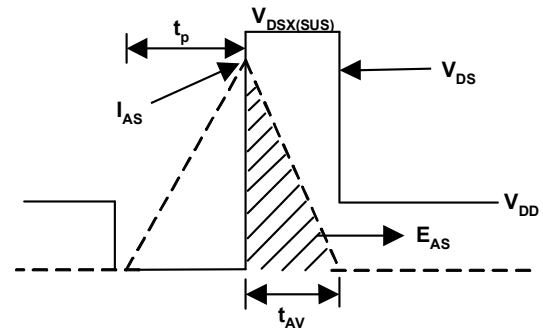
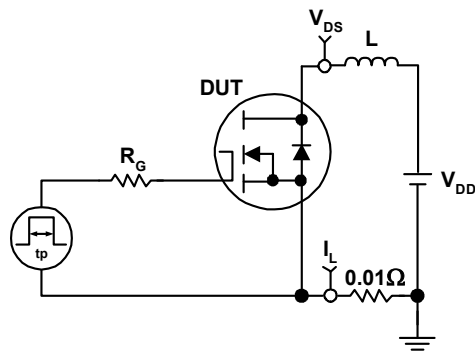
Typical Operating Characteristics (Cont.)



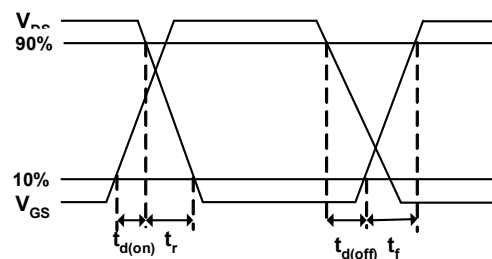
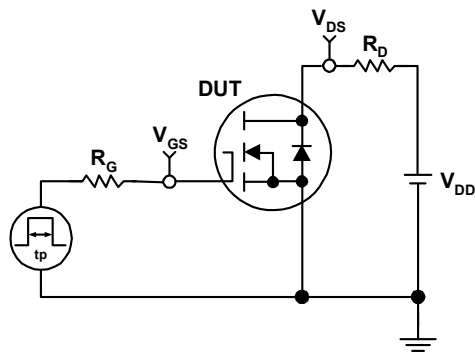
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms

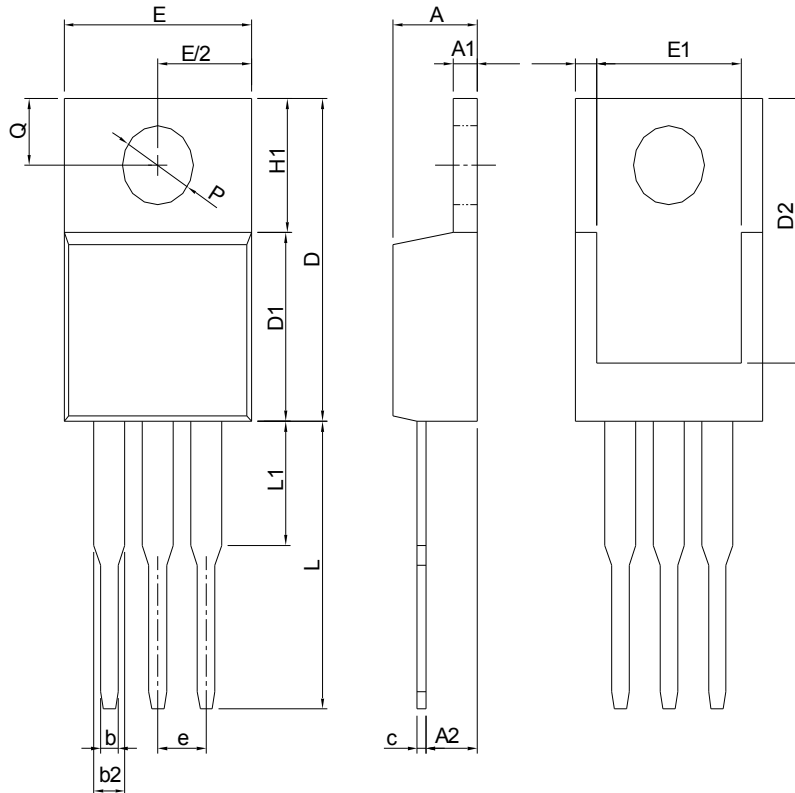


Switching Time Test Circuit and Waveforms



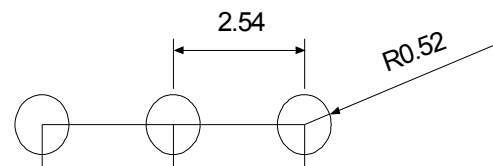
Package Information

TO-220



SYMBOL	TO-220			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.40	0.020	0.055
A2	2.03	2.92	0.080	0.115
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.02	0.330	0.355
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
L	12.70	14.73	0.500	0.580
L1	-	6.35	-	0.250
P	3.53	4.09	0.139	0.161
Q	2.54	3.43	0.100	0.135

RECOMMENDED LAND PATTERN



UNIT: mm

Note: Follow JEDEC TO-220 AB.